

**Amendments to the Specification:**

Please replace the paragraph beginning at page 1, line 14, with the following amended paragraph:

Among LCDs including field-generating electrodes on respective panels, a ~~kind type~~ of ~~LCDs~~ LCD provides a plurality of pixel electrodes arranged in a matrix at on one panel and a common electrode covering an entire surface of the other panel. The image display of the LCD is accomplished by applying individual voltages to the respective pixel electrodes. For the application of the individual voltages, a plurality of three-terminal thin film transistors (TFTs) are connected to the respective pixel electrodes, and a plurality of gate lines transmitting signals for controlling the TFTs and a plurality of data lines transmitting voltages to be applied to the pixel electrodes are provided on the panel.

Please replace the paragraph beginning at page 2, line 1, with the following amended paragraph:

The gate conductor and the data conductor are preferably made of an Al containing metal such as Al and Al alloy having low resistivity for reducing the signal delay in the gate lines and the data lines. The pixel electrodes are usually made of a transparent conductive material such as indium tin oxide (ITO) and indium zinc oxide (IZO) for both the field generation upon voltage application and the light transmission.

Please replace the paragraph beginning at page 2, line 6, with the following amended paragraph:

In the meantime, the contact between Al containing metal and ITO or IZO causes several problems such as corrosion of the Al containing metal and ~~the~~ large contact resistance.

Please delete all of the paragraphs starting from page 10, line 27, which starts with "A TFT array panel for an LCD..." through the paragraph ending at page 15, line 5, which ends with

"In these cases, the contact assistants 192 and 199 may be made of material such as ITO or IZO different from the pixel electrodes 191."

Please replace the paragraph beginning at page 18, line 6, with the following amended paragraph:

Referring to Fig. 9, the third portions of the gate insulating layer 140 and the second portions of the passivation layer 180 are removed to complete the contact holes 182, 185, 187 and 189. The removal of those portions ~~are made~~ is performed by dry etching under the condition that the etching ratios for the gate insulating layer 140 and the passivation layer 180 are substantially equal. Since the thickness of the third portions of the gate insulating layer 140 is smaller than that of the second portions of the passivation layer 180, the third portions of the gate insulating layer 140 and the second portions of the passivation insulating layer 180 are completely removed, and simultaneously, the second portions of the gate insulating layer 140 ~~are remained~~ remain to prevent the undercut of the gate insulating layer 140 under the drain electrodes 175 and the storage capacitor conductors 177.

Please replace the paragraph beginning at page 23, line 8, with the following amended paragraph:

Referring to Figs. 17A and 17B, the third portions of the extrinsic a-Si layer 160 on the areas B2 and of the intrinsic a-Si layer 150 are removed preferably by dry etching and the second portions 314 of the photoresist are removed to expose the second portions of the conductors 174. The removal of the second portions 314 of the photoresist are performed either simultaneously with or independent from the removal of the third portions of the extrinsic a-Si layer 160 and of the intrinsic a-Si layer 150. A gas mixture of SF<sub>6</sub> and HCl or a gas mixture of SF<sub>6</sub> and O<sub>2</sub> can etch the a-Si layers 150 and 160 and the photoresist by nearly the same etching ratio. Residue of the second portions 314 of the photoresist ~~remained~~ remaining on the channel areas C2 is removed by ashing.

Please replace the paragraph beginning at page 24, line 27, with the following amended paragraph:

For descriptive ~~purpose~~ purposes, portions on the areas A3 are called first portions, portions of the passivation layer 180, the drain electrodes 175, the data lines 171, and the gate insulating layer 140 on the active contact areas C3 are called second portions, and portions of the passivation layer 180, the gate insulating layer 140, and the gate lines 121 on the peripheral contact areas B2 are called third portions.

Please replace the paragraph beginning at page 25, line 1, with the following amended paragraph:

As shown in Figs. 20A and 20B, the exposed third portions of the passivation layer 180 on the peripheral contact areas B3 are removed by etching. Although the dry etching may etch out the top portions of the second portions of the passivation layer 180 and the third portions of the gate insulating layer 140, it is preferable that the third portions of the gate insulating layer 140 ~~is~~ are thinner than the second portions of the passivation layer 180 so that the second portions of the gate insulating layer 140 may not be removed in later steps. Residue of the second portions 414 of the photoresist ~~remained~~ remaining on the active contact areas C3 is removed by ashing to completely expose the second portions of the passivation layer 180.

Please replace the paragraph beginning at page 25, line 1, with the following amended paragraph:

Referring to Figs. 21A and 21B, the third portions of the gate insulating layer 140 and the second portions of the passivation layer 180 are removed to complete the contact holes 182, 185 and 189. The removal of those portions are made by dry etching under the condition that the etching ratios for the gate insulating layer 140 and the passivation layer 180 are substantially equal. Since the thickness of the third portions of the gate insulating layer 140 is smaller than that of the second portions of the passivation layer 180, the third portions of the

gate insulating layer 140 and the second portions of the passivation insulating layer 180 are completely removed, and simultaneously, the second portions of the gate insulating layer 140 ~~are remained~~ remain to prevent the undercut of the gate insulating layer 140 under the drain electrodes 175.

Please replace the paragraph beginning at page 26, line 26, with the following amended paragraph:

As described above, the edges of the drain electrodes are exposed with ~~remaining~~ the gate insulating layer remaining under the drain electrodes to prevent the undercut at the signal lines and to ~~smoothing~~ smooth the profiles of the contact portions such that the disconnection of the pixel electrodes is prevented. In addition, the lower film having low contact resistance is exposed to secure the reliability of the contact portions. Furthermore, the upper film having low resistivity is included to improve the quality of the product. Moreover, the manufacturing method is simplified.